



钜地半导体
Tudi Semiconductor

Product Specification

TUDI-SN65LBC184/SN75LBC184

Differential transceiver with transient voltage suppression function

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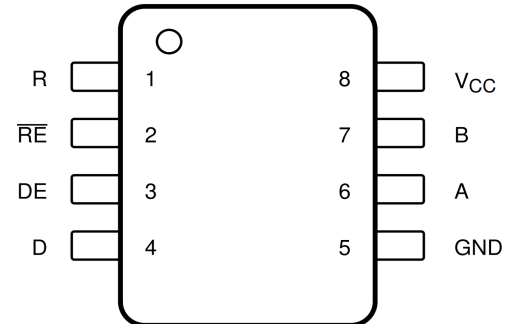
**semiconductor device
manufacturer**

- Design
- research and development
- production
- and sales



Features

- Integrated transient voltage suppression
- ESD protection for bus terminals exceeds:
±30kV IEC 61000-2-2, contact discharge
±30kV IEC 61000-4-2, air gap discharge
±15kV EIA/JEDEC human body model
- 400W peak (typical) circuit damage protection, compliant with IEC 61000-4-5
- Controlled driver output voltage slew rate allows cable stub lengths
- Data rates up to 250kbps in electrically noisy environments
- Open-circuit fault protection receiver design
- 1/4 unit load supports 128 devices on the bus
- Thermal shutdown protection
- Power-up and power-down interference protection
- Each transceiver meets or exceeds the requirements of T/EIA-485 (RS-485) and ISO/IEC 8482:1993(E) standards
- Low disabled current (maximum 300μA)
- Pin compatible with SN75176



Package SOIC Package PDIP
(Top View)

Applications

- Industrial networks
- Utility meters
- Motor control

Description

The SN75LBC184 and SN65LBC184 devices are differential data line transceivers in the-standard SN75176 package, featuring built-in protection against high-energy noise transients. This feature significantly improves reliability, providing better resistance to noise transients coupled the data cable compared to most existing devices. These circuits provide a reliable, low-cost, directly coupled (transformerless) data line interface without the need for any external components. The SN75LBC184 and SN65LBC184 can withstand 400W peak (typical) overvoltage transients. The standard combination specified in IEC 61000-4-5 can simulate overvoltage transients and model unidirectional surges caused by overvoltages from switching operations and secondary lightning transients

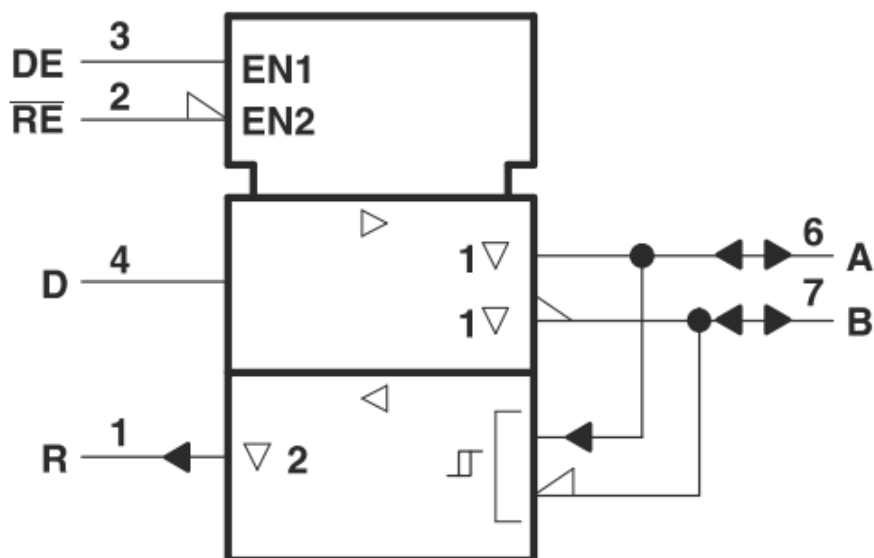


表 4-1. Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
A	6	Bus input/output	Driver output or receiver input (complementary to B)
B	7	Bus input/output	Driver output or receiver input (complementary to A)
D	4	Digital input	Driver data input
DE	3	Digital input	Active-HIGH driver enable
GND	5	Reference potential	Local device ground
R	1	Digital output	Receiver data output
RE	2	Digital input	Active-LOW receiver enable
V _{CC}	8	Supply	4.75V to 5.25V supply



5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage ⁽²⁾	- 0.5	7	V
	Continuous voltage range at any bus terminal	- 15	15	V
	Data input/output voltage	- 0.3	7	V
I _O	Receiver output current	- 20	20	mA
	Continuous total power dissipation ⁽³⁾	Internally Limited		
T _{stg}	Storage temperature		160	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under [§ 5.3](#) is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values, except differential input/output bus voltage, are with respect to network ground terminal.
- (3) The driver shuts down at a junction temperature of approximately 160°C. To operate below this temperature, see the [§ 5.9](#).

5.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	A, B, GND	±15000
			All pins	±3000
		Contact discharge (IEC61000-4-2) ⁽²⁾	A, B, GND ⁽³⁾	±30000
		Air discharge (IEC61000-4-2)	A, B, GND ⁽³⁾	±30000
		All pins (Class 3A)		±8000
		All pins (Class 3B)		±200

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.
- (3) GND and bus pin ESD protection is beyond readily available test equipment capabilities for IEC 61000-4-2, EIA/JEDEC test method A114-A and MIL-STD-883C method 3015. Ratings listed are limits of test equipment; device performance exceeds these limits.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN ⁽¹⁾	TYP	MAX	UNIT
V _{CC}	Supply voltage		4.75	5	5.25	V
V _I or V _{IC}	Voltage at any bus terminal (separately or common mode)		- 7		12	V
V _{IH}	High-level input voltage	D, DE, and $\overline{RE}$	2			V
V _{IL}	Low-level input voltage	D, DE, and RE			0.8	V
V _{ID}	Differential input voltage				12	V
I _{OH}	High-level output current	Driver	- 60			mA
		Receiver	- 8			
I _{OL}	Low-level output current	Driver			60	mA
		Receiver			4	
T _A	Operating free-air temperature	SN75LBC184	0		70	°C
		SN65LBC184	- 40		85	

- (1) The algebraic convention, in which the less-positive (more-negative) limit is designated minimum, is used in this data sheet.



5.4 Thermal Information

THERMAL METRIC ⁽¹⁾		P (PDIP)	D (SOIC)	UNIT
		8 PINS		
R _{θ JA}	Junction-to-ambient thermal resistance	108.7	116.3	°C/W
R _{θ JC(top)}	Junction-to-case (top) thermal resistance	34.8	41.3	°C/W
R _{θ JB}	Junction-to-board thermal resistance	23.6	61.4	°C/W
ψ _{JT}	Junction-to-top characterization parameter	12	4.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	23.5	60.3	°C/W
R _{θ JC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.



5.5 Electrical Characteristics: Driver

over recommended operating conditions (unless otherwise noted)

PARAMETER	ALTERNATE SYMBOLS	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I_{CC} Supply current	NA	DE = RE = 5V No Load		12	25	mA
		DE = 0 V RE = 5V No Load		175	300	μ A
I_{IH} High-level input current (D, DE, RE)	NA	$V_I = 2.4V$			50	μ A
I_{IL} Low-level input current (D, DE, RE)	NA	$V_I = 0.4V$	- 50			μ A
I_{OS} Short-circuit output current OS ⁽²⁾	NA	$V_O = -7V$	- 250	- 120		mA
		$V_O = V_{CC}$			250	
		$V_O = 12V$			250	
I_{OZ} High-impedance output current	NA	See Receiver I_I				mA
V_O Output voltage	V_{Oa}, V_{Ob}	$I_O = 0$	0		V_{CC}	V
$V_{OC(PP)}$ Peak-to-peak change in common-mode output voltage during state transitions	NA	See 图 6-4 and 图 6-5		0.8		V
V_{OC} Common-mode output voltage	$ V_{os} $	See 图 6-3	1		3	V
$ \Delta V_{OC(SS)} $ Magnitude of change, common-mode steady-state output voltage	$ V_{os} - V_{os} $	See 图 6-5			0.1	V
$ V_{OD} $ Magnitude of differential output voltage $ V_A - V_B $	V_O	$I_O = 0$	1.5		6	V
		$R_L = 54\Omega$, See 图 6-3	1.5			V
$\Delta V_{OD} $ Change in differential voltage magnitude between logic states	$ V_I - V_I $	$R_L = 54\Omega$			0.1	V

(1) All typical values are measured with $T_A = 25^\circ C$ and $V_{CC} = 5V$.

(2) This parameter is measured with only one output being driven at a time.

5.6 Electrical Characteristics: Receiver

over recommended operation conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
I_{CC} Supply current (total package)	DE = RE = 0 V, No Load			3.9	mA
	RE = 5V, DE = 0 V, No Load			300	μ A
I_I Input current	Other input = 0 V	$V_I = 12V$		250	μ A
		$V_I = 12V, V_{CC} = 0$		250	
		$V_I = -7V$	- 200		
		$V_I = -7V, V_{CC} = 0$	- 200		
I_{OZ} High-impedance-state output current	$V_O = 0.4V$ to $2.4V$			± 100	μ A
V_{hys} Input hysteresis voltage			70		mV
V_{IT+} Positive-going input threshold voltage				200	mV
V_{IT-} Negative-going input threshold voltage		- 200			mV
V_{OH} High-level output voltage	$I_{OH} = -8mA$, See 图 6-6	2.8			V



5.6 Electrical Characteristics: Receiver (续)

over recommended operation conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{OL} Low-level output voltage	$I_{OL} = 4\text{mA}$, See 图 6-6			0.4	V

(1) All typical values are at $V_{CC} = 5\text{V}$, $T_A = 25^\circ\text{C}$.

5.7 Driver Switching Characteristics

over recommended operating conditions (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(DH)}$ Differential output delay time, low-to-high-level output	$R_L = 54\Omega$ $C_L = 50\text{pF}$ See 图 6-4			1.3	μs
$t_{d(DL)}$ Differential output delay time, high-to-low-level output				1.3	μs
t_{PLH} Propagation delay time, low-to-high-level output			0.5	1.3	μs
t_{PHL} Propagation delay time, high-to-low-level output			0.5	1.3	μs
$t_{sk(p)}$ Pulse skew ($ t_{d(DH)} - t_{d(DL)} $)			75	150	ns
t_r Rise time, single-ended		0.25		1.2	μs
t_f Fall time, single-ended		0.25		1.2	μs
t_{PZH} Output enable time to high level	$R_L = 110\Omega$ See 图 6-1			3.5	μs
t_{PZL} Output enable time to low level	$R_L = 110\Omega$ See 图 6-2			3.5	μs
t_{PHZ} Output disable time from high level	$R_L = 110\Omega$ See 图 6-1			2	μs
t_{PLZ} Output disable time from low level	$R_L = 110\Omega$ See 图 6-2			2	μs

5.8 Receiver Switching Characteristics

over recommended operating conditions (unless otherwise noted)

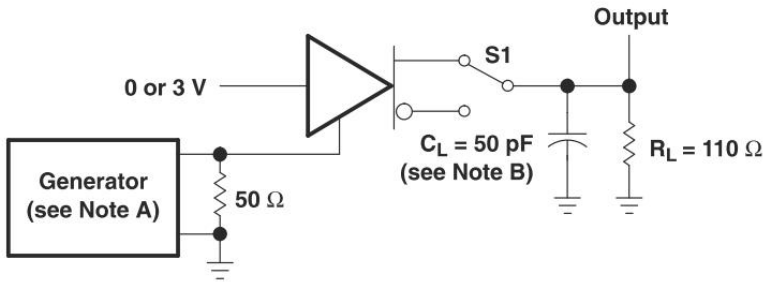
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH} Propagation delay time, low-to-high-level output	$C_L = 50\text{pF}$, See 图 6-6			150	ns
t_{PHL} Propagation delay time, high-to-low-level output				150	ns
$t_{sk(p)}$ Pulse skew ($ t_{PHL} - t_{PLH} $)				50	ns
t_r Rise time, single-ended	See 图 6-6		20		ns
t_f Fall time, single-ended			20		ns
t_{PZH} Output enable time to high level	See 图 6-7			100	ns
t_{PZL} Output enable time to low level				100	ns
t_{PHZ} Output disable time from high level				100	ns
t_{PLZ} Output disable time from low level				100	ns

5.9 Dissipation Ratings

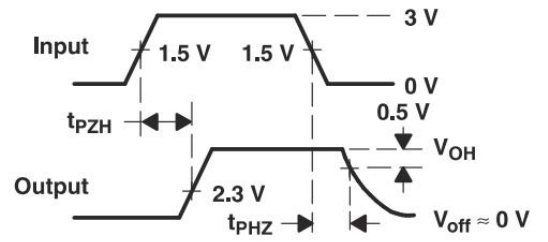
PACKAGE	$T_A \leq 25^\circ\text{C}$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25^\circ\text{C}$	$T_A = 70^\circ\text{C}$ POWER RATING	$T_A = 85^\circ\text{C}$ POWER RATING
D	725 mW	5.8 mW/ $^\circ\text{C}$	464 mW	377 mW
P	1150 mW	9.2 mW/ $^\circ\text{C}$	736 mW	598 mW



6 Parameter Measurement Information



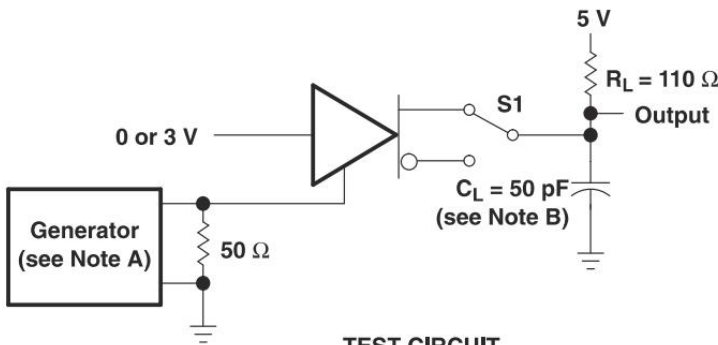
TEST CIRCUIT



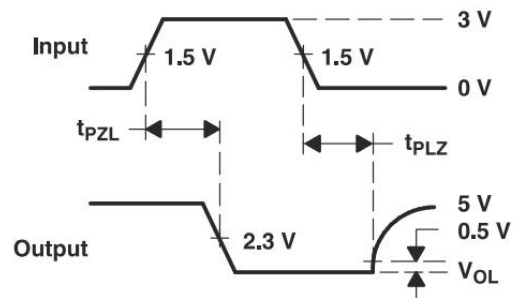
VOLTAGE WAVEFORMS

- A. The input pulse is supplied by a generator having the following characteristics: PRR = 1.25 kHz, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_O = 50 \Omega$.
- B. C_L includes probe and jig capacitance.

图 6-1. Driver t_{PZH} and t_{PHZ} Test Circuit and Voltage Waveforms



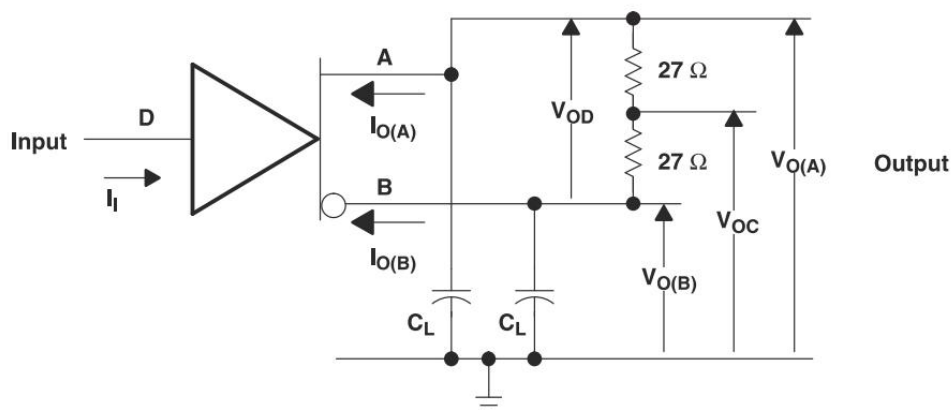
TEST CIRCUIT



VOLTAGE WAVEFORMS

- A. The input pulse is supplied by a generator having the following characteristics: PRR = 1.25 kHz, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_O = 50 \Omega$.
- B. C_L includes probe and jig capacitance.

图 6-2. Driver t_{PZL} and t_{PLZ} Test Circuit and Voltage Waveforms



- A. Resistance values are in ohms and are 1% tolerance.
- B. C_L includes probe and jig capacitance.

图 6-3. Driver Test Circuit, Voltage, and Current Definitions

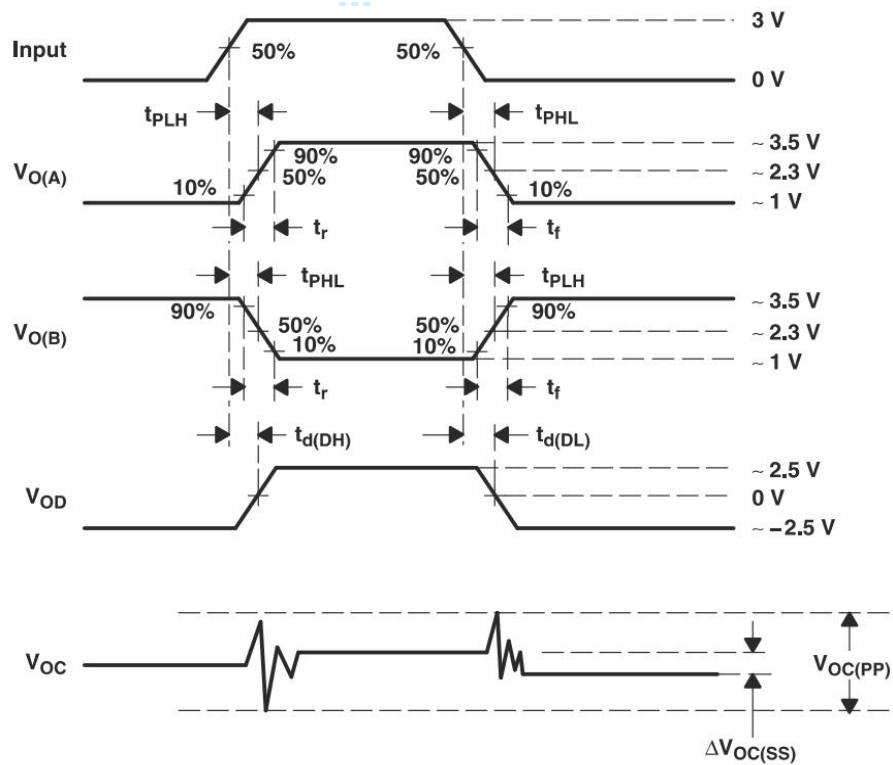
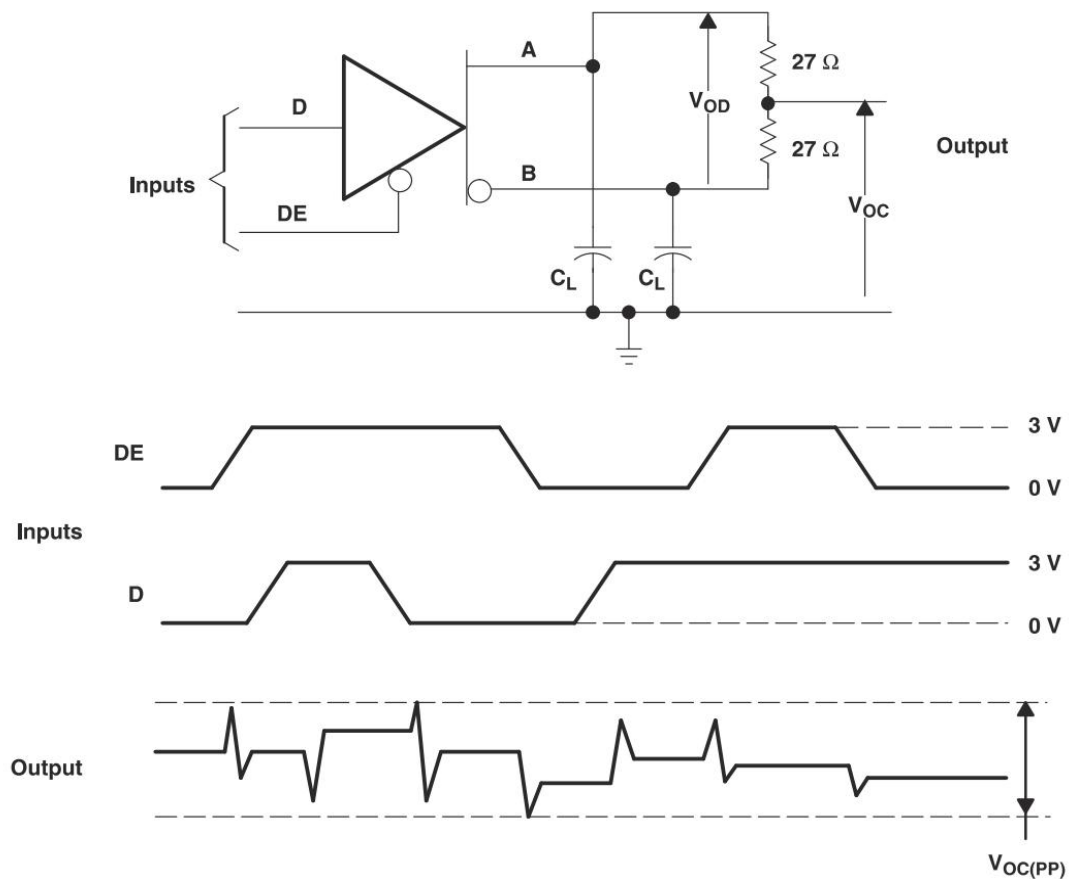


图 6-4. Driver Timing, Voltage, and Current Waveforms

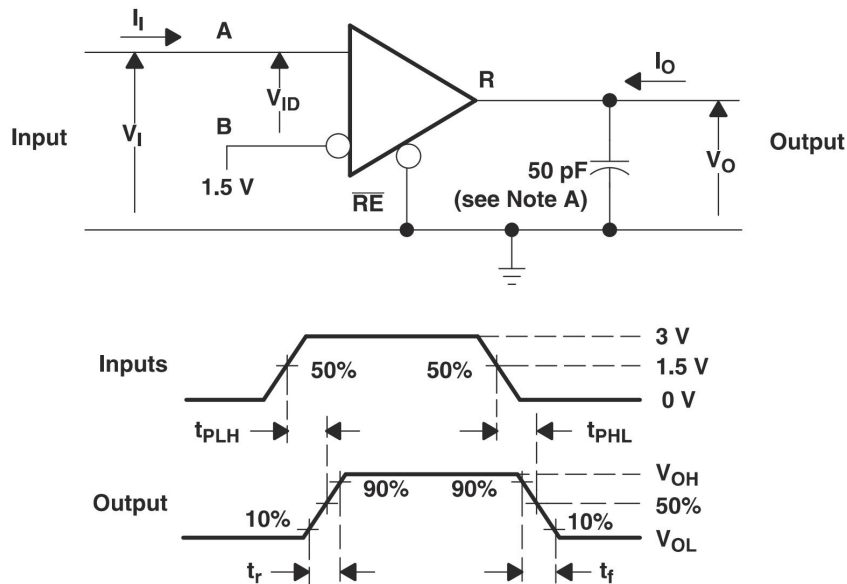


A. Resistance values are in ohms and are 1% tolerance.



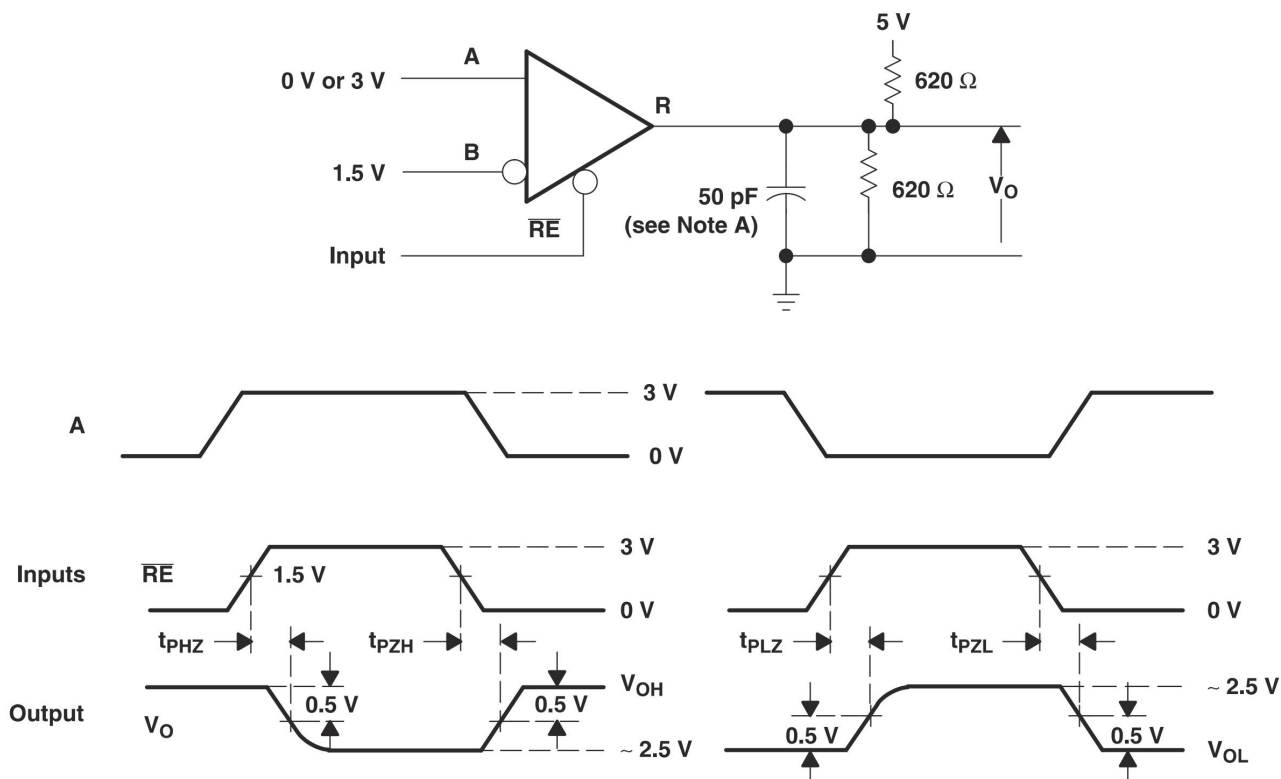
B. C_L includes probe and jig capacitance ($\pm 10\%$).

图 6-5. Driver $V_{OC(PP)}$ Test Circuit and Waveforms



A. This value includes probe and jig capacitance ($\pm 10\%$).

图 6-6. Receiver t_{PLH} and t_{PHL} Test Circuit and Voltage Waveforms



A. This value includes probe and jig capacitance ($\pm 10\%$).

图 6-7. Receiver t_{PZL} , t_{PLZ} , t_{PZH} , and t_{PHZ} Test Circuit and Voltage Waveforms



7 Detailed Description

7.1 Overview

The SNx5LBC184 device is a 5V, half-duplex, RS-485 transceiver with integrated transient voltage suppressors that prevent circuit damage in the presence of high-energy transients of up to 400W peak power. This transceiver has an active-HIGH driver enable and active-LOW receiver enable. The differential driver is suitable for data transmission up to 250kbps.

7.2 Functional Block Diagram

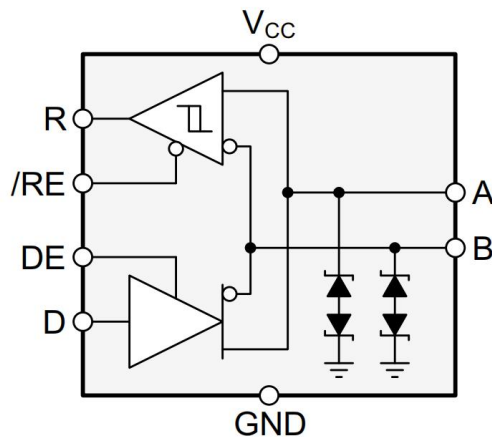


图 7-1. Functional Logic Diagram

7.3 Feature Description

Integrated transient voltage suppressors protect the transceiver against Electrostatic Discharges (ESD) according to IEC 61000-4-2 of up to $\pm 30\text{kV}$ and surge transients according to IEC 61000-4-5 of up to 400W peak.

The differential driver incorporates slew-rate controlled outputs sufficient to transmit data up to 250kbps. Slew-rate control allows for longer unterminated cable runs and longer stub lengths from the main cable trunk than with faster voltage transitions. A unique receiver design provides a high level failsafe output when the inputs are left floating.

The SN65LBC184 is characterized from -40°C to 85°C and the SN75LBC184 is characterized from 0°C to 70°C .



7.4 Device Functional Modes

When the driver enable pin (DE) is logic high, the differential outputs A and B follow the logic states at data input D. A logic high at D causes A to turn high and B to turn low. In this case, the differential output voltage defined as $V_{OD} = V_A - V_B$ is positive. When D is low, the output states reverse, B turns high, A becomes low, and V_{OD} is negative.

When DE is low, both outputs turn high-impedance. In this condition, the logic state at D is irrelevant.

表 7-1. Driver Functions

INPUT ⁽¹⁾	ENABLE	OUTPUTS		FUNCTION
D	DE	A	B	
H	H	H	L	Actively drive bus High
L	H	L	H	Actively drive bus Low
X	L	Z	Z	Driver disabled

(1) H = high level, L = low level, ? = indeterminate, X = irrelevant, Z = high impedance (off)

When the receiver enable pin, $\overline{RE}$, is logic low, the receiver is enabled. When the differential input voltage defined as $V_{ID} = V_A - V_B$ is positive and higher than the positive input threshold, V_{IT+} , the receiver output (R) turns high. When V_{ID} is negative and lower than the negative input threshold, V_{IT-} , the receiver output turns low. If V_{ID} is between V_{IT+} and V_{IT-} , the output is indeterminate.

When $\overline{RE}$ is logic high, the receiver output is high-impedance and the magnitude and polarity of V_{ID} are irrelevant. When the transceiver is disconnected from the bus, the receiver provides a failsafe high output.

表 7-2. Receiver Functions

DIFFERENTIAL INPUT	ENABLE ⁽¹⁾	OUTPUT	FUNCTION
$V_{ID} = V_A - V_B$	$\overline{RE}$	R	
$V_{ID} > V_{IT+}$	L	H	Receive valid bus High
$V_{IT-} < V_{ID} < V_{IT+}$	L	?	Indeterminate bus state
$V_{ID} < V_{IT-}$	L	L	Receive valid bus Low
X	H	Z	Receiver disabled
OPEN	L	H	Receiver failsafe High

(1) H = high level, L = low level, ? = indeterminate, X = irrelevant, Z = high impedance (off)

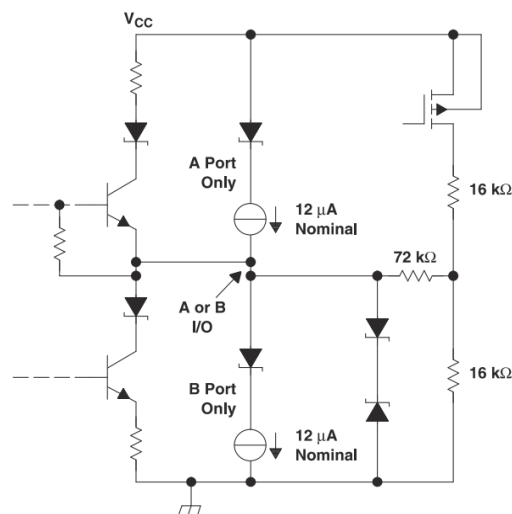


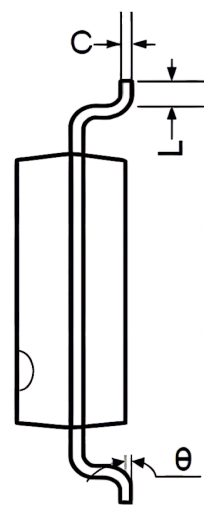
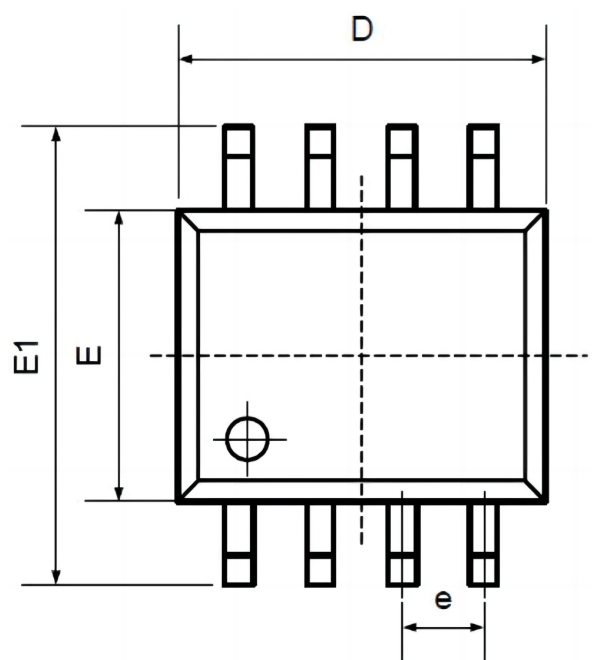
图 7-2. Schematic of Inputs and Outputs



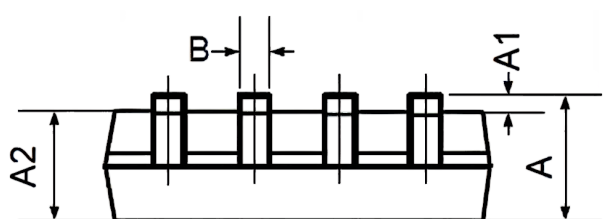
Order information

Order Number	Package	Package Quantity	Marking On The park
SN65LBC184DR-TUDI	SOP8	Tape,Reel,2500	SN65LBC184DR
SN65LBC184P-TUDI	DIP8	Tube,50,A box of 2000	SN65LBC184P
SN75LBC184DR-TUDI	SOP8	Tape,Reel,2500	SN75LBC184DR
SN75LBC184P-TUDI	DIP8	Tube,50,A box of 2000	SN75LBC184P

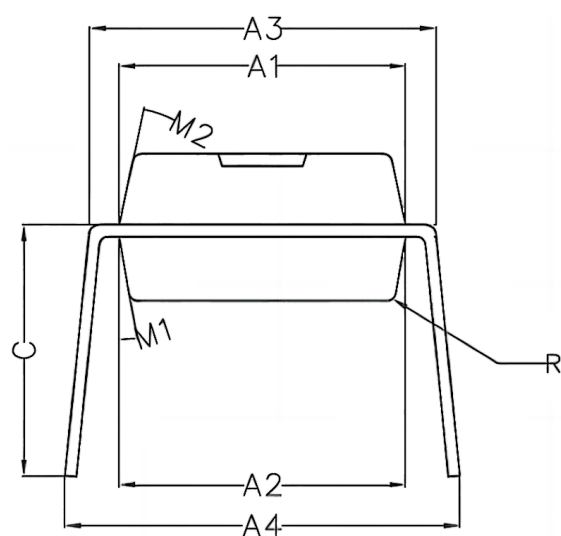
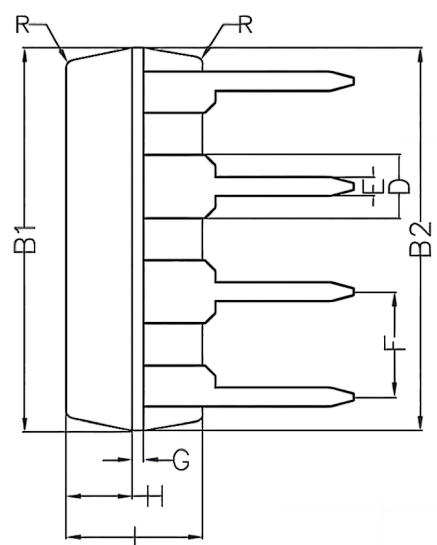
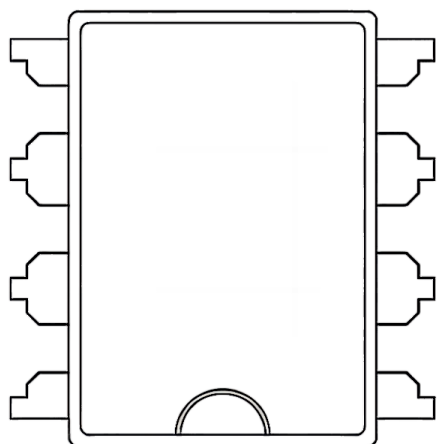
Package SOP8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
B	0.330	0.510	0.013	0.020
C	0.190	0.250	0.007	0.010
D	4.780	5.000	0.188	0.197
E	3.800	4.000	0.150	0.157
E1	5.800	6.300	0.228	0.248
e	1.270TYP		0.050TYP	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Package DIP8



Symbol	Min	Non	Max
A1	6.28	6.33	6.38
A2	6.33	6.38	6.43
A3	7.52	7.62	7.72
A4	7.80	8.40	9.00
B1	9.15	9.20	9.25
B2	9.20	9.25	9.30
C		5.57	
D		1.52	
E	0.43	0.45	0.47
F		2.54	
G		0.25	
H	1.54	1.59	1.64
I	3.22	3.27	3.32
R		0.20	
M1	9°	10°	11°
M2	11°	12°	13°



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